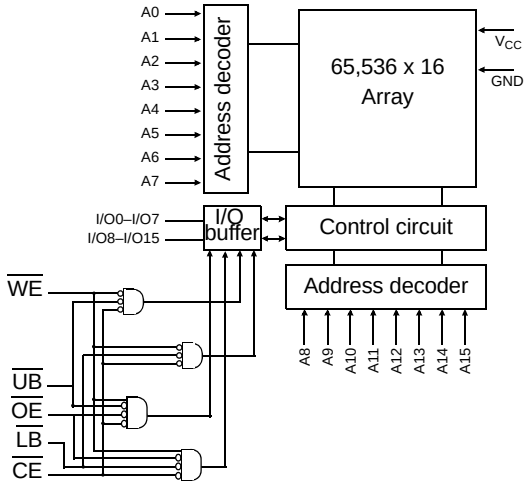
# 5 V 64K X 16 CMOS SRAM

## Features

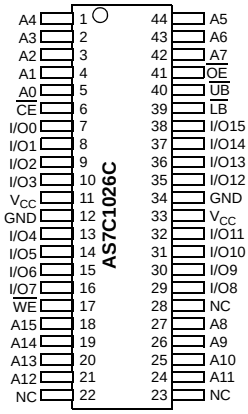
- Industrial (-40$^{o}$ to 85$^{o}$C) temperature
- Organization: 65,536 words × 16 bits
- Center power and ground pins for low noise
- High speed
  - 12 ns address access time
  - 6 ns output enable access time
- Low power consumption via chip deselect
- Easy memory expansion with $\overline{CE}$, $\overline{OE}$ inputs
- TTL-compatible, three-state I/O
- Upper and Lower byte pin
- JEDEC standard packaging
  - 44-pin 400 mil SOJ
  - 44-pin TSOP 2-400
- ESD protection ≥ 2000 volts

## Logic block diagram




## Pin arrangement

44-Pin SOJ (400 mil), TSOP 2



## Functional description

The AS7C1026C is a 5V high-performance CMOS 1,048,576-bit Static Random Access Memory (SRAM) device organized as 65,536 words × 16 bits. It is designed for memory applications where fast data access, low power, and simple interfacing are desired.

Equal address access and cycle times ($t_{AA}$, $t_{RC}$, $t_{WC}$) of 12 ns with output enable access times ($t_{OE}$) of 6 ns are ideal for high-performance applications.

When $\overline{CE}$ is high, the device enters standby mode. If inputs are still toggling, the device will consume $I_{SB}$ power. If the bus is static, then full standby power is reached ($I_{SB1}$).

A write cycle is accomplished by asserting write enable ($\overline{WE}$) and chip enable ($\overline{CE}$). Data on the input pins I/O0 through I/O15 is written on the rising edge of $\overline{WE}$ (write cycle 1) or $\overline{CE}$ (write cycle 2). To avoid bus contention, external devices should drive I/O pins only after outputs have been disabled with output enable ($\overline{OE}$) or write enable ($\overline{WE}$).

A read cycle is accomplished by asserting output enable ($\overline{OE}$) and chip enable ($\overline{CE}$) with write enable ($\overline{WE}$) high. The chip drives I/O pins with the data word referenced by the input address. When either chip enable or output enable is inactive or write enable is active, output drivers stay in high-impedance mode.

The device provides multiple center power and ground pins, and separate byte enable controls, allowing individual bytes to be written and read. $\overline{LB}$ controls the lower bits, I/O0 through I/O7, and $\overline{UB}$ controls the higher bits, I/O8 through I/O15.

All chip inputs and outputs are TTL-compatible, and operation is from a single 5 V supply. The AS7C1026C is packaged in common industry standard packages.

## Absolute maximum ratings

| Parameter | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| Voltage on $V_{CC}$ relative to GND | $V_{t1}$ | –0.50 | +7.0 | V |
| Voltage on any pin relative to GND | $V_{t2}$ | –0.50 | $V_{CC}$ +0.50 | V |
| Power dissipation | $P_D$ | – | 1.25 | W |
| Storage temperature (plastic) | $T_{stg}$ | –55 | +125 | °C |
| Ambient temperature with VCC applied | $T_{bias}$ | –55 | +125 | °C |
| DC current into outputs (low) | $I_{OUT}$ | – | 50 | mA |

**Note:**

Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

## Truth table

| $\overline{CE}$ | $\overline{WE}$ | $\overline{OE}$ | $\overline{LB}$ | $\overline{UB}$ | I/O0–I/O7 | I/O8–I/O15 | Mode |
|---|---|---|---|---|---|---|---|
| H | X | X | X | X | High Z | High Z | Standby ($I_{SB}$), $I_{SBI}$) |
| L | H | L | L | H | $D_{OUT}$ | High Z | Read I/O0–I/O7 ($I_{CC}$) |
| L | H | L | H | L | High Z | $D_{OUT}$ | Read I/O8–I/O15 ($I_{CC}$) |
| L | H | L | L | L | $D_{OUT}$ | $D_{OUT}$ | Read I/O0–I/O15 ($I_{CC}$) |
| L | L | X | L | L | $D_{IN}$ | $D_{IN}$ | Write I/O0–I/O15 ($I_{CC}$) |
| L | L | X | L | H | $D_{IN}$ | High Z | Write I/O0–I/O7 ($I_{CC}$) |
| L | L | X | H | L | High Z | $D_{IN}$ | Write I/O8–I/O15 ($I_{CC}$) |
| L<br>L | H<br>X | H<br>X | X<br>H | X<br>H | High Z | High Z | Output disable ($I_{CC}$) |

**Key:** H = high, L = low, X = don't care.

## Recommended operating conditions

| Parameter | Symbol | Min | Nominal | Max | Unit |
|---|---|---|---|---|---|
| Supply voltage | $V_{CC}$ | 4.5 | 5.0 | 5.5 | V |
| Input voltage | $V_{IH}$ | 2.2 | – | $V_{CC}$ + 0.5 | V |
| | $V_{IL}$ | –0.5 | – | 0.8 | V |
| Ambient operating temperature (Industrial) | $T_A$ | –40 | – | 85 | $^{o}$ C |

**Notes:**

$V_{IL}$ min = -1.5V for pulse width less than 5ns, once per cycle.

$V_{IH}$ max = $V_{CC}$+2.0V for pulse width less than 5ns, once per cycle.

## DC operating characteristics (over the operating range)[1]

| Parameter | Sym | Test conditions | AS7C1026C-12 | | Unit |
|---|---|---|---|---|---|
| | | | Min | Max | |
| Input leakage current | $\lvert I_{LI} \rvert$ | $V_{CC}$ = Max, $V_{IN}$ = GND to $V_{CC}$ | – | 5 | µA |
| Output leakage current | $\lvert I_{LO} \rvert$ | $V_{CC}$ = Max, $\overline{CE}$ = $V_{IH}$, $V_{OUT}$ = GND to $V_{CC}$ | – | 5 | µA |
| Operating power supply current | $I_{CC}$ | $V_{CC}$ = Max, $\overline{CE} \le V_{IL}$, $I_{OUT}$ = 0mA, f = $f_{Max}$ | – | 210 | mA |
| Standby power supply current | $I_{SB}$ | $V_{CC}$ = Max, $\overline{CE} \ge V_{IH}$, f = $f_{Max}$ | – | 60 | mA |
| | $I_{SB1}$ | $V_{CC}$ = Max, $\overline{CE} \ge V_{CC}$–0.2 V, $V_{IN} \le 0.2$ V or $V_{IN} \ge V_{CC}$–0.2 V, f = 0 | – | 10 | mA |
| Output voltage | $V_{OL}$ | $I_{OL}$ = 8 mA, $V_{CC}$ = Min | – | 0.4 | V |
| | $V_{OH}$ | $I_{OH}$ = –4 mA, $V_{CC}$ = Min | 2.4 | – | V |

## Capacitance (f = 1MHz, $T_a$ = 25 °C, $V_{CC}$ = NOMINAL)[2]

| Parameter | Symbol | Signals | Test conditions | Max | Unit |
|---|---|---|---|---|---|
| Input capacitance | $C_{IN}$ | A, $\overline{CE}$, $\overline{WE}$, $\overline{OE}$, $\overline{LB}$, $\overline{UB}$ | $V_{IN}$ = 0 V | 6 | pF |
| I/O capacitance | $C_{I/O}$ | I/O | $V_{OUT}$ = 0 V | 7 | pF |

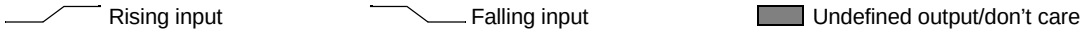
**Note:**

This parameter is guaranteed by device characterization, but is not production tested.

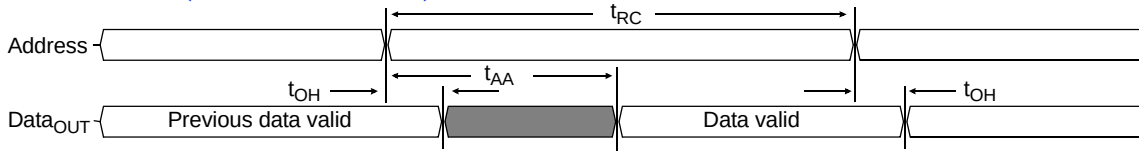
## Read cycle (over the operating range)[3,9]

| Parameter | Symbol | AS7C1026C-12 | | Unit | Notes |
|---|---|---|---|---|---|
| | | Min | Max | | |
| Read cycle time | $t_{RC}$ | 12 | – | ns | |
| Address access time | $t_{AA}$ | – | 12 | ns | 3 |
| Chip enable ($\overline{CE}$) access time | $t_{ACE}$ | – | 12 | ns | 3 |
| Output enable ($\overline{OE}$) access time | $t_{OE}$ | – | 7 | ns | |
| Output hold from address change | $t_{OH}$ | 4 | – | ns | 5 |
| $\overline{CE}$ low to output in low Z | $t_{CLZ}$ | 4 | – | ns | 4, 5 |
| $\overline{CE}$ high to output in high Z | $t_{CHZ}$ | – | 6 | ns | 4, 5 |
| $\overline{OE}$ low to output in low Z | $t_{OLZ}$ | 0 | – | ns | 4, 5 |
| Byte select access time | $t_{BA}$ | – | 7 | ns | |
| Byte select Low to low Z | $t_{BLZ}$ | 0 | – | ns | 4, 5 |
| Byte select High to high Z | $t_{BHZ}$ | – | 6 | ns | 4, 5 |
| $\overline{OE}$ high to output in high Z | $t_{OHZ}$ | – | 6 | ns | 4, 5 |
| Power up time | $t_{PU}$ | 0 | – | ns | 4, 5 |
| Power down time | $t_{PD}$ | – | 12 | ns | 4, 5 |

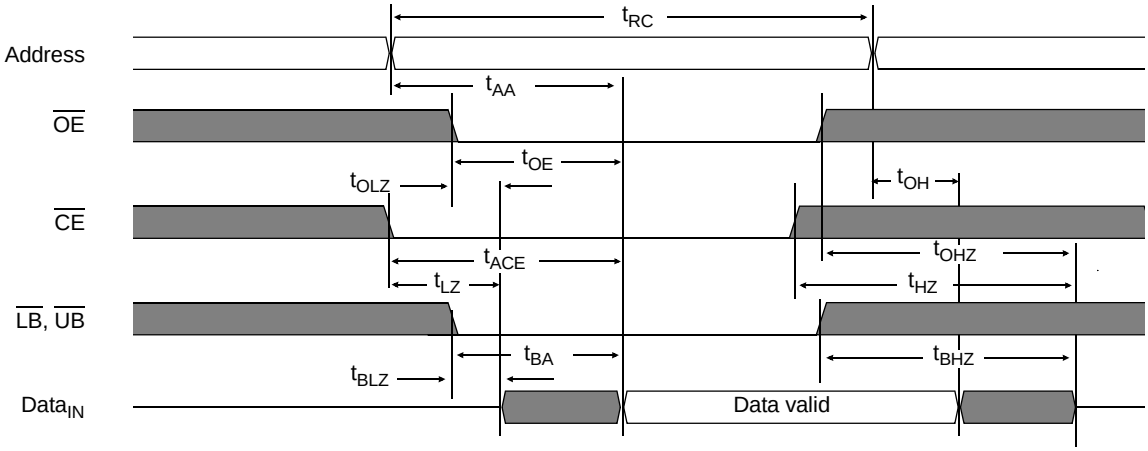
## Key to switching waveforms




## Read waveform 1 (address controlled)[3,6,7,9]



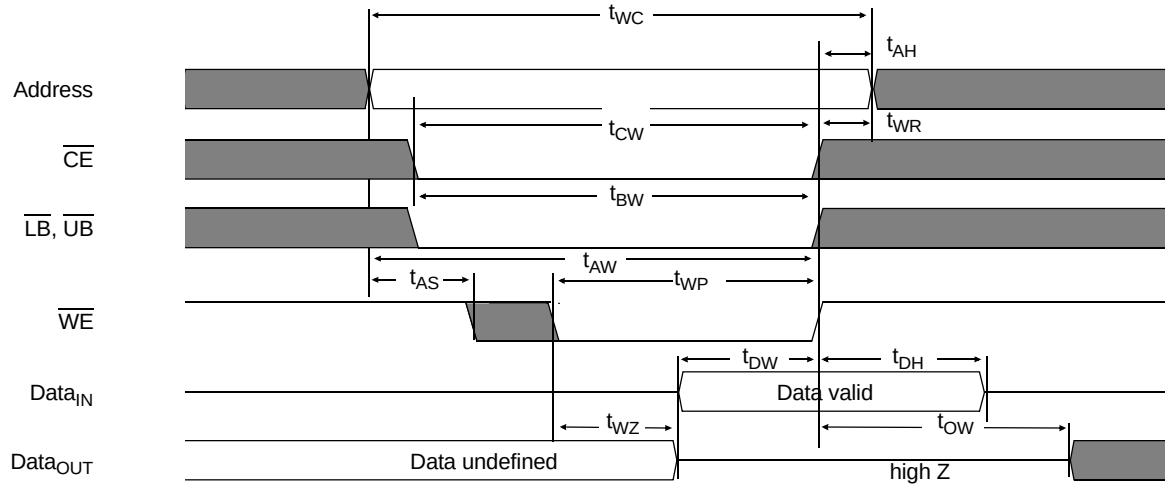

## Read waveform 2 ($\overline{OE}$, $\overline{CE}$, $\overline{UB}$, $\overline{LB}$ controlled)[3,6,8,9]



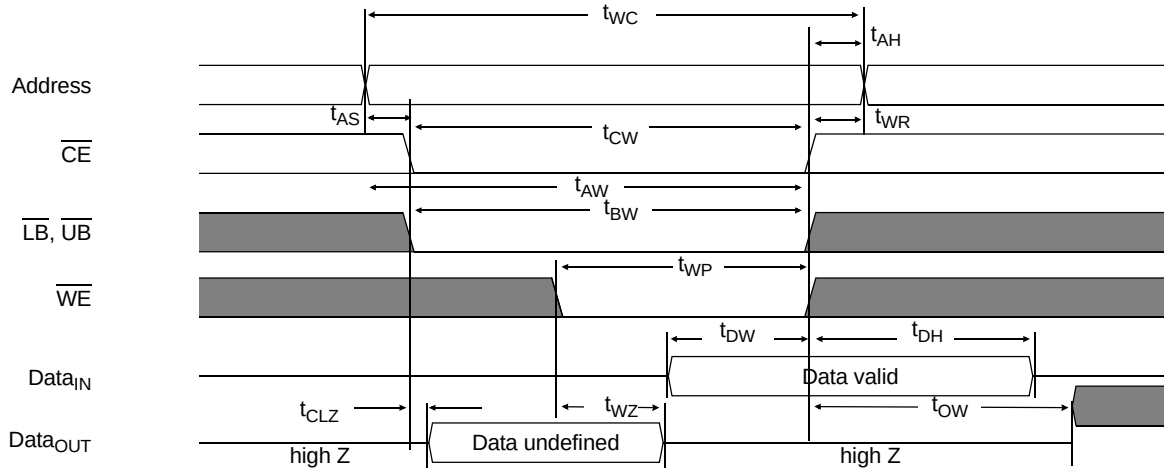
## Write cycle (over the operating range) [11]

| Parameter | Symbol | AS7C1026C-12 | | Unit | Notes |
|---|---|---|---|---|---|
| | | Min | Max | | |
| Write cycle time | $t_{WC}$ | 12 | – | ns | |
| Chip enable ($\overline{CE}$) to write end | $t_{CW}$ | 9 | – | ns | |
| Address setup to write end | $t_{AW}$ | 9 | – | ns | |
| Address setup time | $t_{AS}$ | 0 | – | ns | |
| Write pulse width | $t_{WP}$ | 9 | – | ns | |
| Write recovery time | $t_{WR}$ | 0 | – | ns | |
| Address hold from end of write | $t_{AH}$ | 0 | – | ns | |
| Data valid to write end | $t_{DW}$ | 7 | – | ns | |
| Data hold time | $t_{DH}$ | 0 | – | ns | 5 |
| Write enable to output in high Z | $t_{WZ}$ | – | 6 | ns | 4, 5 |
| Output active from write end | $t_{OW}$ | 1 | – | ns | 4, 5 |
| Byte select low to end of write | $t_{BW}$ | 9 | – | ns | |

## Write waveform 1 ($\overline{WE}$ controlled)[11]



## Write waveform 2 ($\overline{CE}$ controlled)[11]




## AC test conditions

- Output load: see Figure B.
- Input pulse level: GND to 3.0 V. See Figure A.
- Input rise and fall times: 3 ns. See Figure A.
- Input and output timing reference levels: 1.5

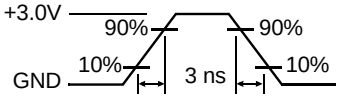



Figure A: Input pulse

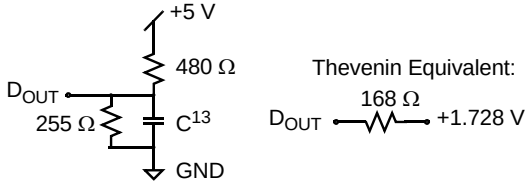
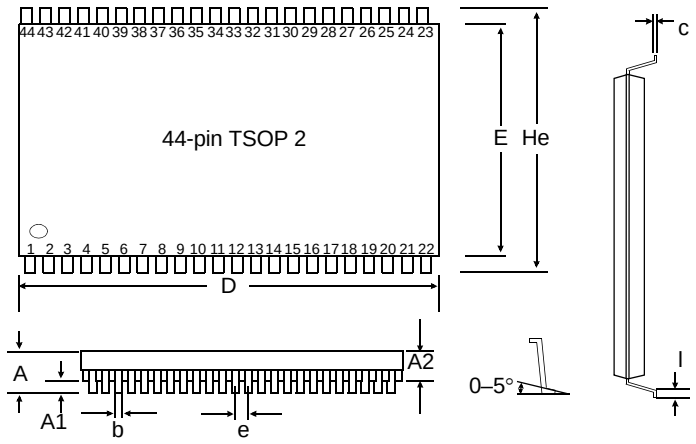



Figure B: 5 V Output load

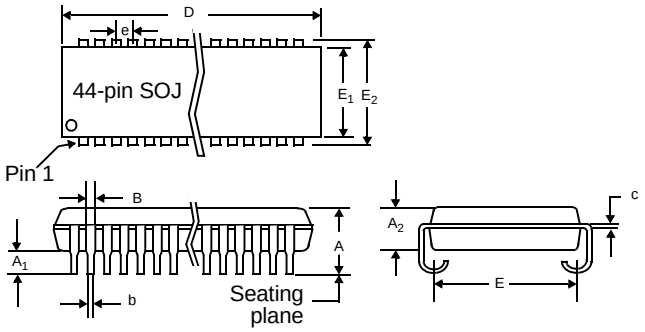
### Notes:

1 During $V_{CC}$ power-up, a pull-up resistor to $V_{CC}$ on $\overline{CE}$ is required to meet $I_{SB}$ specification.
2 This parameter is sampled, but not 100% tested.
3 For test conditions, see *AC Test Conditions*, Figures A and B.
4 These parameters are specified with $C_L$ = 5 pF, as in Figures B. Transition is measured ± 200 mV from steady-state voltage.
5 This parameter is guaranteed, but not tested.
6 $\overline{WE}$ is high for read cycle.
7 $\overline{CE}$ and $\overline{OE}$ are low for read cycle.
8 Address is valid prior to or coincident with $\overline{CE}$ transition low.
9 All read cycle timings are referenced from the last valid address to the first transitioning address.
10 N/A.
11 All write cycle timings are referenced from the last valid address to the first transitioning address.
12 Not applicable.
13 C = 30 pF, except all high Z and low Z parameters where C = 5 pF.

## Package dimensions




| | 44-pin TSOP 2 | |
|---|---|---|
| | Min (mm) | Max (mm) |
| A | | 1.2 |
| A1 | 0.05 | 0.15 |
| A2 | 0.95 | 1.05 |
| b | 0.30 | 0.45 |
| c | 0.120 | 0.21 |
| D | 18.31 | 18.52 |
| E | 10.06 | 10.26 |
| He | 11.68 | 11.94 |
| e | 0.80 (typical) | |
| l | 0.40 | 0.60 |



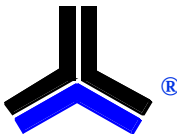

| | 44-pin SOJ 400 mil | |
|---|---|---|
| | Min (in) | Max (in) |
| A | 0.128 | 0.148 |
| $A_1$ | 0.025 | – |
| $A_2$ | 0.105 | 0.115 |
| B | 0.026 | 0.032 |
| b | 0.015 | 0.020 |
| c | 0.007 | 0.013 |
| D | 1.120 | 1.130 |
| E | 0.370 NOM | |
| $E_1$ | 0.395 | 0.405 |
| $E_2$ | 0.435 | 0.445 |
| e | 0.050 NOM | |

## Ordering codes

| Package | Volt/Temp | 12 ns |
|---|---|---|
| Plastic SOJ, 400 mil | 5V Industrial | AS7C1026C-12JIN |
| TSOP 2, 10.2 x 18.4 mm | 5V Industrial | AS7C1026C-12TIN |

## Part numbering system

| AS7C | 1026C | –XX | X | X | X |
|---|---|---|---|---|---|
| SRAM prefix | Device number | Access time | Package:<br>J = SOJ 400 mil<br>T = TSOP 2, 10.2 x 18.4 mm | Temperature range:<br>I = industrial: -40° C to 85° C | N = LEAD FREE PART |



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